1. General description

PNP/PNP general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- · Low collector capacitance
- Low collector-emitter saturation voltage
- · Closely matched current gain
- · Reduces number of components and board space
- No mutual interference between the transistors
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

· General-purpose switching and amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V _{CEO}	collector-emitter voltage	open base	-	-	-65	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	110	-	-	



65 V, 100 mA PNP/PNP general-purpose transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	D. D. D.	C1 B2 E2
2	B1	base TR1	6 5 4	
3	C2	collector TR2		(TR1 TR2)
4	E2	emitter TR2		
5	B2	base TR2	∐1 ∐2 ∐3	
6	C1	collector TR1	TSSOP6 (SOT363)	sym138

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BC856S-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
BC856S-Q	5F%

[1] % = placeholder for manufacturing site code

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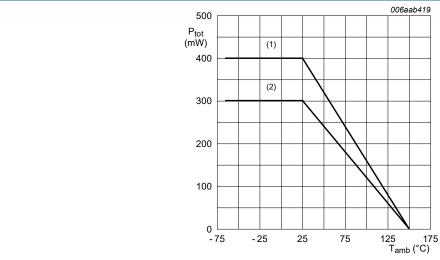
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or		•			
V _{CBO}	collector-base voltage	open emitter		-	-80	V
V _{CEO}	collector-emitter voltage	open base		-	-65	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	220	mW
			[2]	-	250	mW
Per device				'		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	400	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm²
- (2) FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curves SOT363 (SC-88)

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or				'		
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	[1]	-	-	568	K/W
		[2]	-	-	500	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	230	K/W
Per device	,			•			
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	416	K/W
junct	junction to ambient		[2]	-	-	313	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².

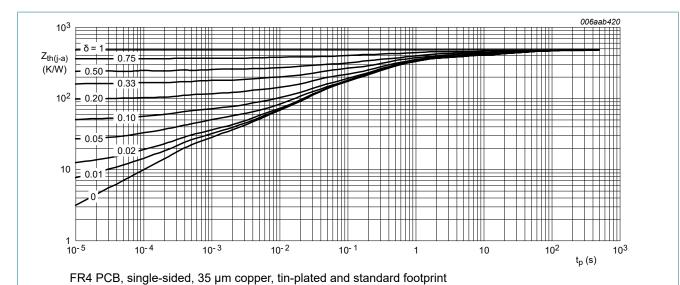
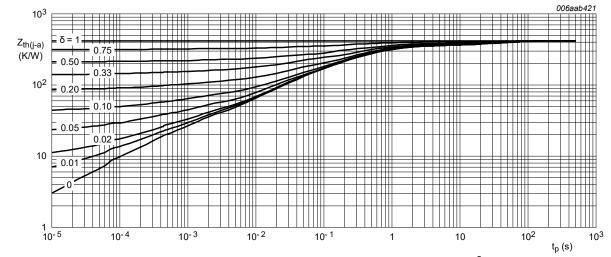


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm²

Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-80	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = -2 mA; I _B = 0 A; T _{amb} = 25 °C	-65	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = -100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	-5	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-15	nA
	current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	110	-	-	
V _{CEsat}	collector-emitter	I _C = -10 mA; I _B = -0.5 mA; T _{amb} = 25 °C	-	-	-100	mV
	saturation voltage	I_C = -100 mA; I_B = -5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-300	mV
V _{BEsat}	base-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	700	-	mV
V _{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	-600	-650	-750	mV
		V _{CE} = -5 V; I _C = -10 mA; T _{amb} = 25 °C	-	-	-820	mV
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	2.5	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz

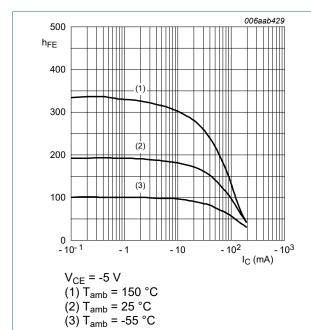


Fig. 4. Per transistor: DC current gain as a function of collector current; typical values

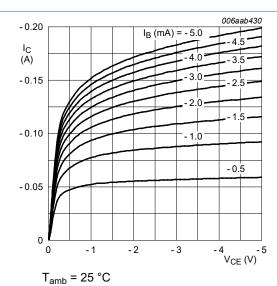


Fig. 5. Per transistor: Collector current as a function of collector-emitter voltage; typical values

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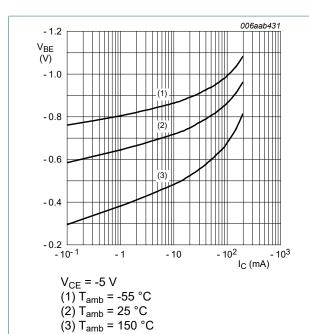


Fig. 6. Per transistor: Base-emitter voltage as a function of collector current; typical values

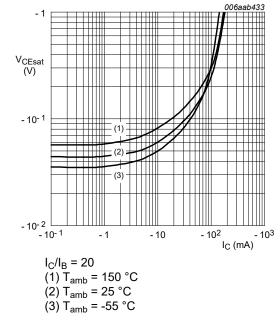
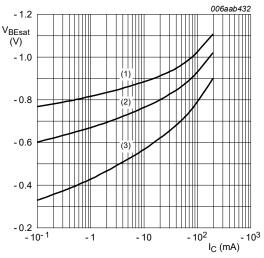


Fig. 8. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 150 \,^{\circ}C$

Fig. 7. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values

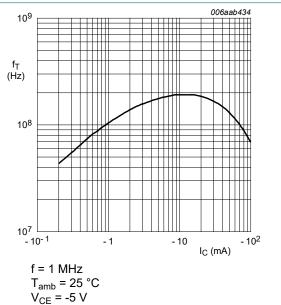


Fig. 9. Per transistor: Transition frequency as a function of collector current; typical values

11. Test information

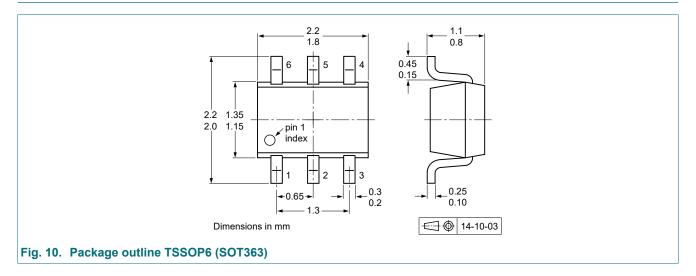
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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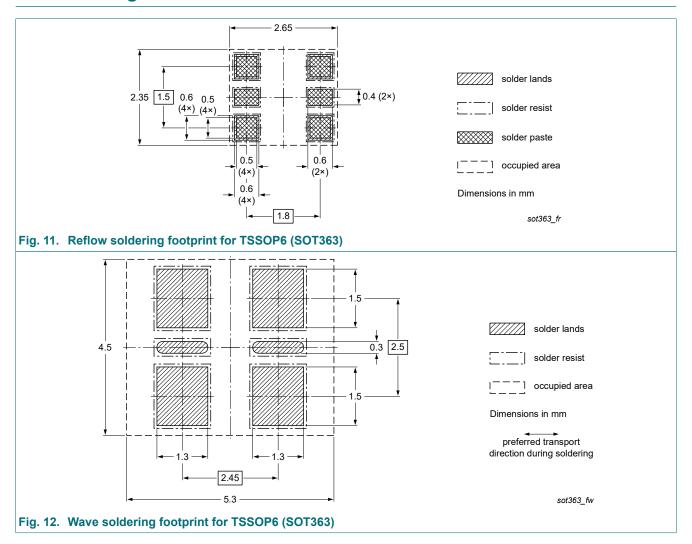
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC856S-Q v.1	20210617	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 17 June 2021

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